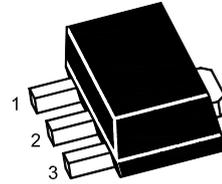


SOT-89 Plastic-Encapsulate Transistors

TRANSISTOR (NPN)

FEATURES

- Small Flat Package
- High Breakdown Voltage
- Excellent h_{FE} Linearity



1.Base 2.Collector 3.Emitter
SOT-89 Plastic Package

MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	400	V
V_{CEO}	Collector-Emitter Voltage	400	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current	200	mA
P_C	Collector Power Dissipation	500	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	250	$^\circ\text{C/W}$
T_j	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55~+150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=10\mu\text{A}, I_E=0$	400			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}, I_B=0$	400			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=10\mu\text{A}, I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=300\text{V}, I_E=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=4\text{V}, I_C=0$			0.1	μA
DC current gain	h_{FE}	$V_{CE}=10\text{V}, I_C=50\text{mA}$	60		200	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=50\text{mA}, I_B=5\text{mA}$			0.6	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=50\text{mA}, I_B=5\text{mA}$			1	V
Transition frequency	f_T	$V_{CE}=30\text{V}, I_C=10\text{mA}$		70		MHz
Collector output capacitance	C_{ob}	$V_{CB}=30\text{V}, I_E=0, f=1\text{MHz}$		4		pF

CLASSIFICATION OF h_{FE}

RANK	D	E
RANGE	60 - 120	100 - 200
MARKING	CN	